PHP52N06T

N-channel TrenchMOS standard level FET

Rev. 02 — 25 February 2010 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies
- Uninterruptible power supplies

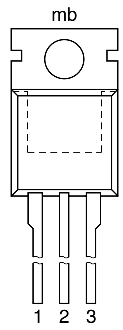
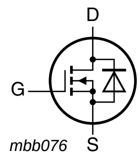
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	60	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; see Figure 3 and 1	-	-	52	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	-	120	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10$ V; $I_D = 40$ A; $V_{DS} = 44$ V; $T_j = 25$ °C; see Figure 11	-	11.5	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 175$ °C; see Figure 9 and 10	-	-	44	mΩ
		$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; see Figure 9 and 10	-	17	22	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 **SOT78 (TO-220AB)**	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

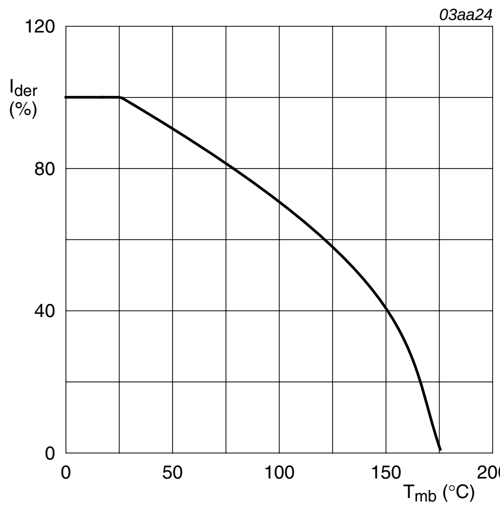
Type number	Package		
	Name	Description	Version
PHP52N06T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

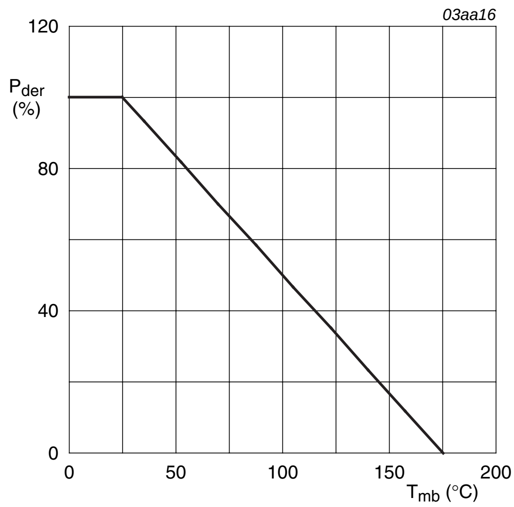
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ	-	60	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 100$ °C; see Figure 1	-	37	A
		$V_{GS} = 10$ V; $T_{mb} = 25$ °C; see Figure 3 and 1	-	52	A
I_{DM}	peak drain current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C; see Figure 3	-	208	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	120	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25$ °C	-	52	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C	-	208	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 48$ A; $V_{sup} \leq 55$ V; $R_{GS} = 50$ Ω; unclamped	-	115	mJ



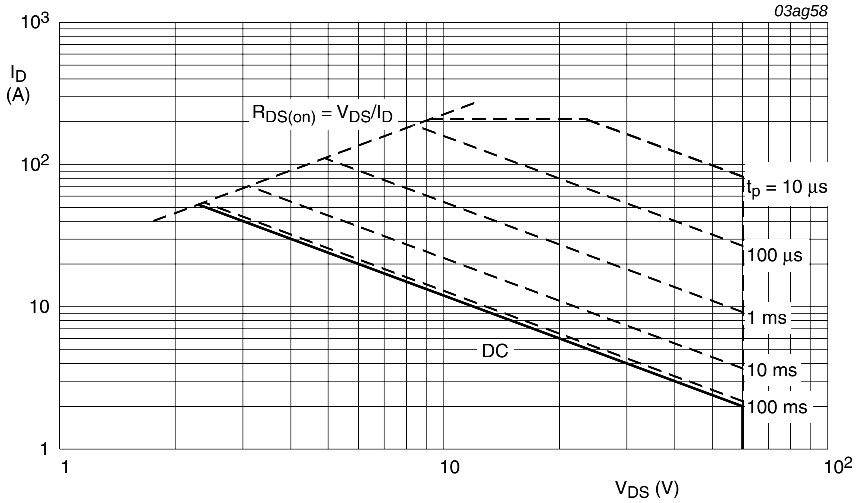
$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25°C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.25	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

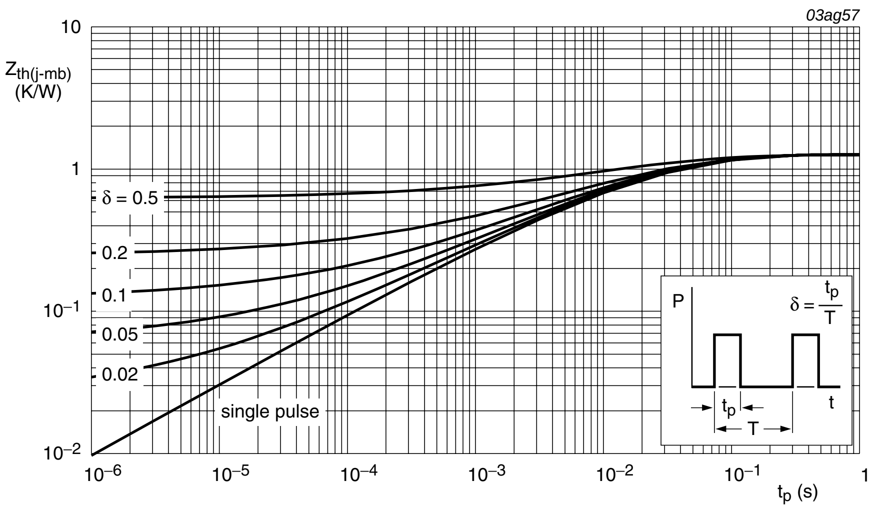
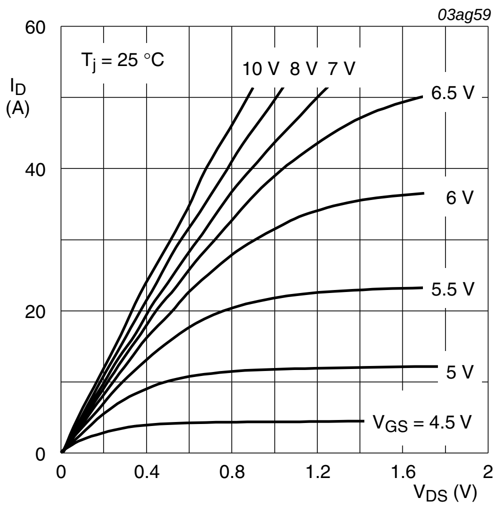


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration

6. Characteristics

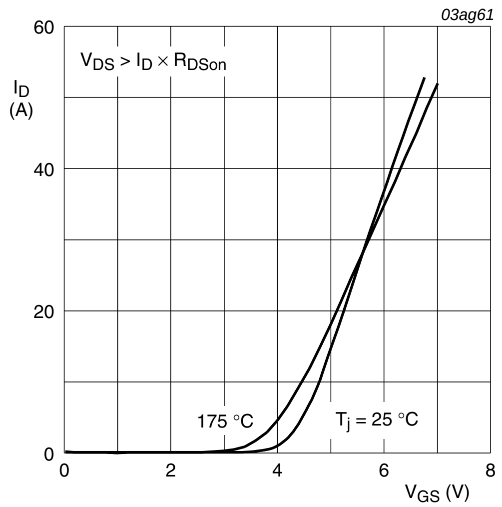
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	55	-	-	V
		I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 8	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 8	-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 8	2	3	4	V
I_{DSS}	drain leakage current	V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	µA
		V_{DS} = 55 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 9 and 10	-	-	44	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 9 and 10	-	17	22	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 40 A; V_{DS} = 44 V; V_{GS} = 10 V; T_j = 25 °C; see Figure 11	-	36	-	nC
Q_{GS}	gate-source charge		-	8.4	-	nC
Q_{GD}	gate-drain charge		-	11.5	-	nC
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 12	-	1200	1592	pF
C_{oss}	output capacitance		-	290	356	pF
C_{rss}	reverse transfer capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; T_j = 25 °C; see Figure 12	-	179	240	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω; T_j = 25 °C	-	15	-	ns
t_r	rise time		-	74	-	ns
$t_{d(off)}$	turn-off delay time		-	70	-	ns
t_f	fall time		-	40	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 20 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 13	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	45	-	ns
Q_r	recovered charge		-	110	-	nC



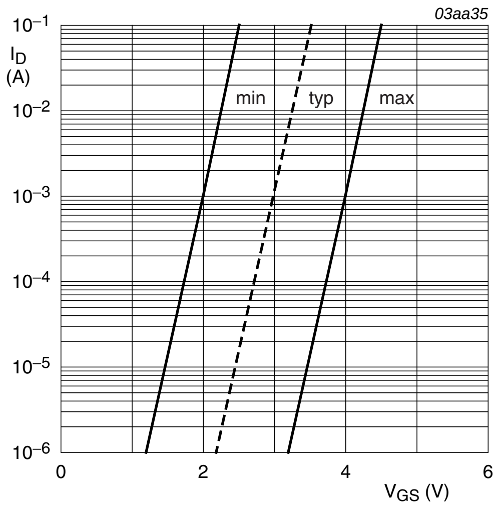
$T_j = 25°C; t_p = 300 \mu s$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



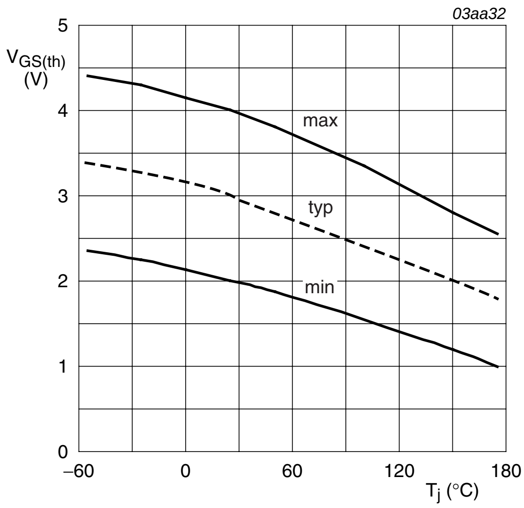
$T_j = 25°C$ and $175°C; V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



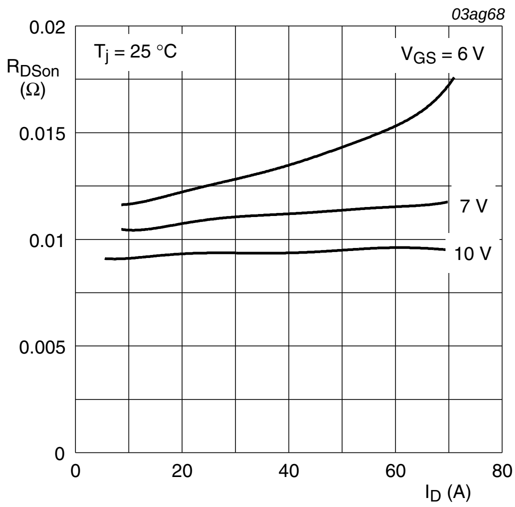
$T_j = 25°C; V_{DS} = 5V$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



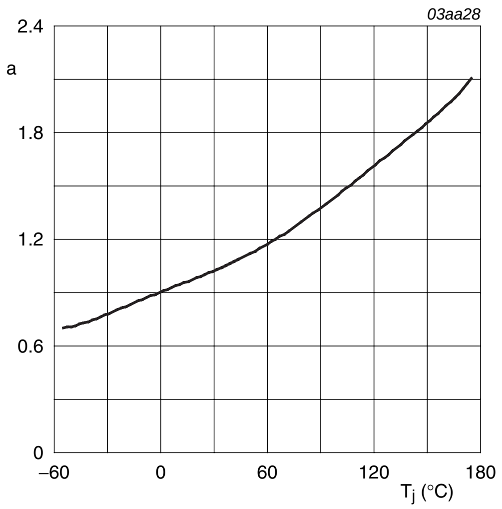
$I_D = 1mA; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature



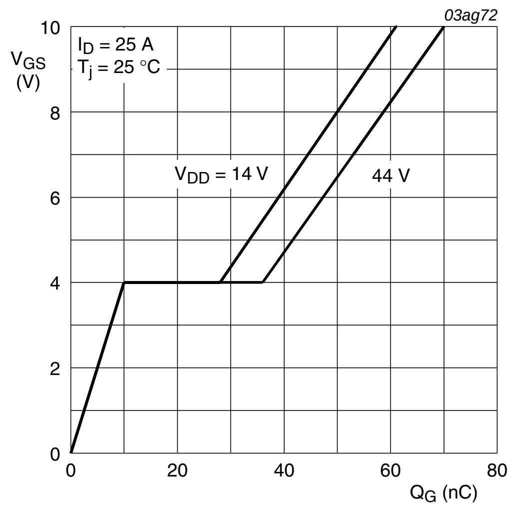
$T_j = 25°C$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



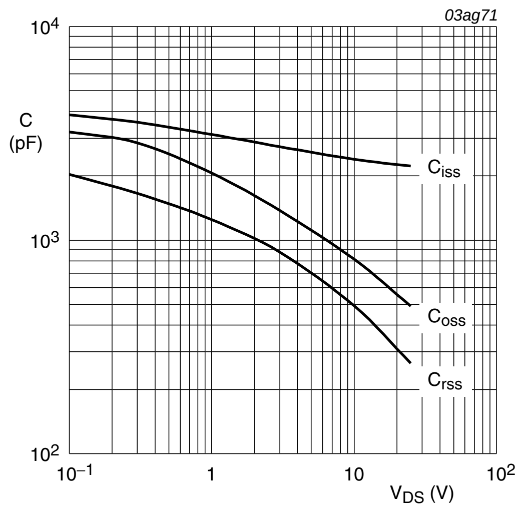
$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



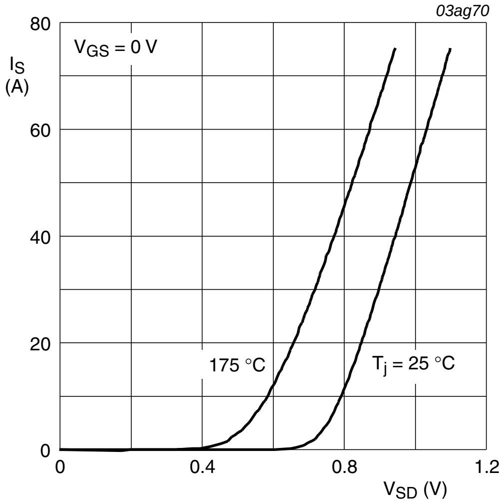
$T_j = 25°C; I_D = 40A$

Fig 11. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

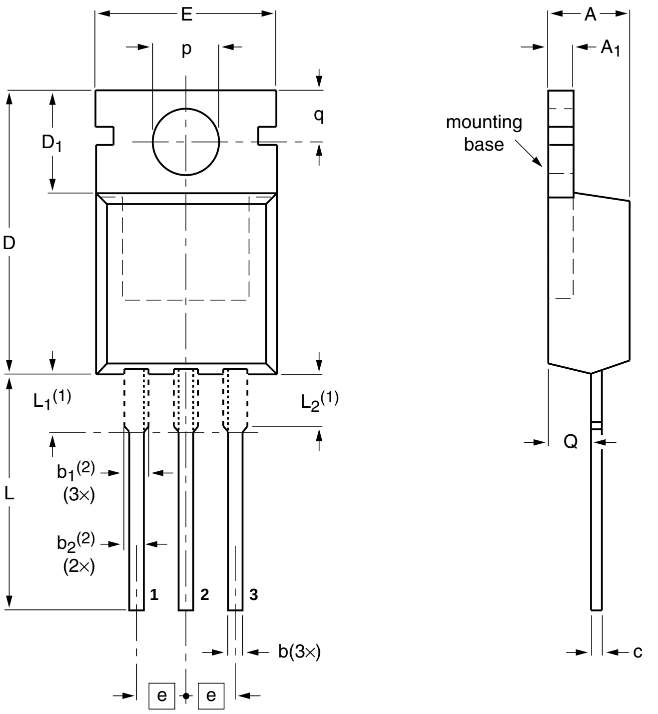


$V_{GS} = 0V$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1(2)	b_2(2)	c	D	D_1	E	e	L	L_1(1)	L_2(1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

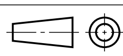
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig 14. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP52N06T_2	20100225	Product data sheet	-	PHP52N06T_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
PHP52N06T_1	20020109	Product data	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

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